

**Gate resistor installed
Dual N-channel MOSFET**

**KFCAB21260L
Data Sheet**

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1. GENERAL DESCRIPTION

Gate resistor installed Dual N-channel MOSFET
 For lithium-ion secondary battery protection circuits

2. FEATURES

- Source-source On-state resistance: RSS (on) typ. = 2.0 mΩ (VGS = 4.5 V)
- CSP (Chip Size Package)
- RoHS compliant (EU RoHS / MSL: Level 1 compliant)

3. MARKING SYMBOL: 3E

4. PACKAGING

Embossed type (Thermo-compression sealing): 8,000 pcs / reel (standard)

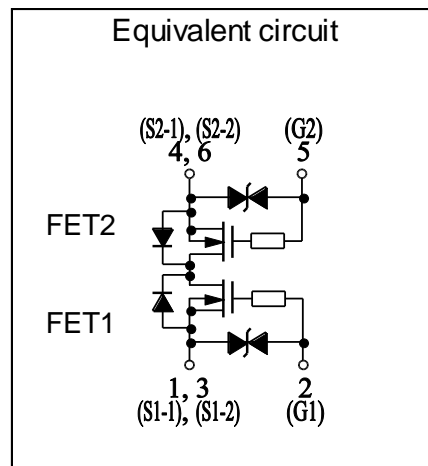
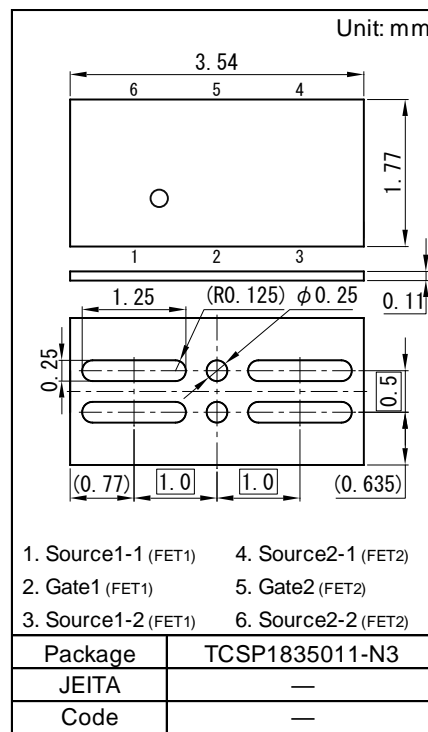
5. ABSOLUTE MAXIMUM RATINGS Ta = 25 °C

Parameter	Symbol	Rating	Unit
Source-source Voltage	VSS	12	V
Gate-source Voltage	VGS	±8	V
Source Current	DC *1	IS1	A
	DC *2	IS2	
	Pulsed *3	ISp	
Total Power Dissipation	DC *1	PD1	W
	DC *2	PD2	
Channel Temperature	Tch	150	°C
Storage Temperature Range	Tstg	-55 to +150	°C

6. THERMAL CHARACTERISTICS Ta = 25 °C

Parameter	Symbol	Rating	Unit
Thermal Resistance (ch-a)	Rth1 *1	278	°C / W
	Rth2 *2	59	

- Note *1 Mounted on FR4 board (25.4 mm x 25.4 mm x t1.0 mm) using the minimum recommended pad size (36 μm Copper).
 *2 Mounted on Ceramic substrate (70 mm x 70 mm x t1.0 mm).
 *3 t = 10 μs, Duty Cycle ≤ 1 %



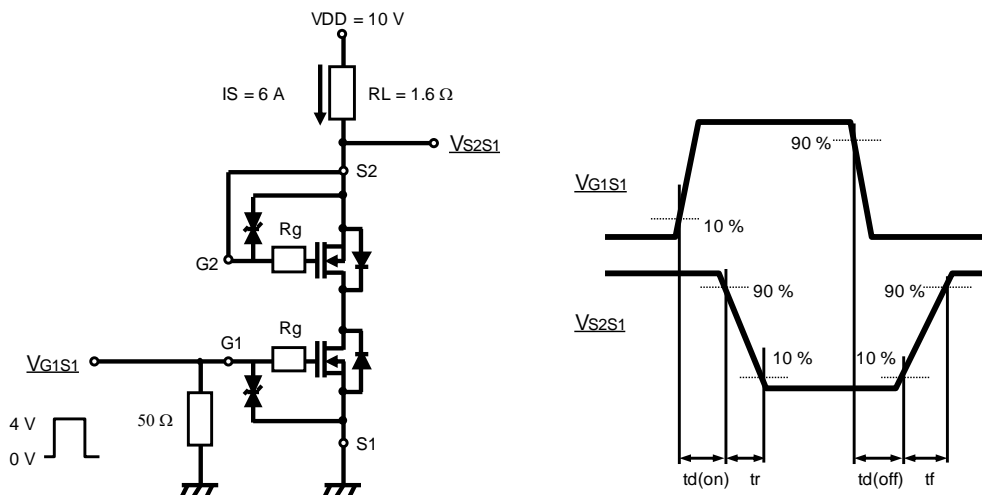
7. ELECTRICAL CHARACTERISTICS Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Source-source Breakdown Voltage	VSSS	IS = 1 mA, VGS = 0 V	12			V
Zero Gate Voltage Source Current	ISSS	VSS = 12 V, VGS = 0 V			1.0	μA
Gate-source Leakage Current	IGSS1	VGS = ±8 V, VSS = 0 V			±10	μA
	IGSS2	VGS = ±5 V, VSS = 0 V			±1.0	
Gate-source Threshold Voltage	Vth	IS = 1.64 mA, VSS = 10 V	0.35	0.90	1.40	V
Source-source On-state Resistance	RSS(on)1	IS = 6.0 A, VGS = 4.5 V	1.50	2.00	2.65	mΩ
	RSS(on)2	IS = 6.0 A, VGS = 3.8 V	1.60	2.20	2.85	
	RSS(on)3	IS = 6.0 A, VGS = 3.1 V	1.65	2.40	3.95	
	RSS(on)4	IS = 6.0 A, VGS = 2.5 V	1.90	3.10	6.10	
Body Diode Forward Voltage	VF(s-s)	IF = 6.0 A, VGS = 0 V		0.8	1.2	V
Input Capacitance *1	Ciss	VSS = 10 V, VGS = 0 V, f = 1 kHz		4950		pF
Output Capacitance *1	Coss			770		
Reverse Transfer Capacitance *1	Crss			690		
Turn-on Delay Time *1,*2	td(on)		VDD = 10 V, VGS = 0 to 4 V		2.1	
Rise Time *1,*2	tr	IS = 6.0 A		3.3		
Turn-off Delay Time *1,*2	td(off)	VDD = 10 V, VGS = 4 to 0 V		12.1		μs
Fall Time *1,*2	tf	IS = 6.0 A		6.9		
Total Gate Charge *1	Qg	VDD = 10 V		49		nC
Gate-source Charge *1	Qgs	VGS = 0 to 4 V		11		
Gate-drain Charge *1	Qgd	IS = 6.0 A		17		

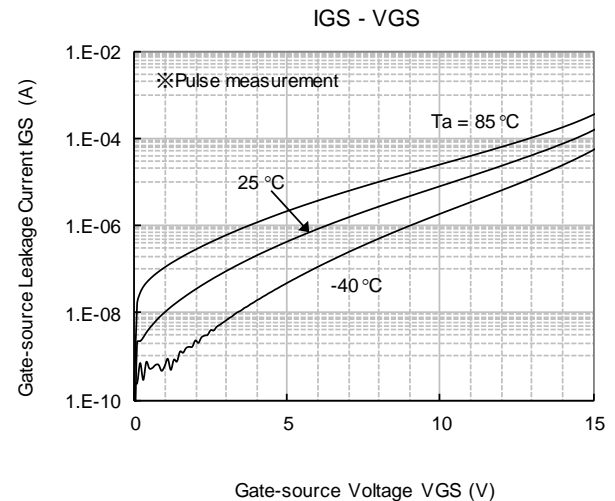
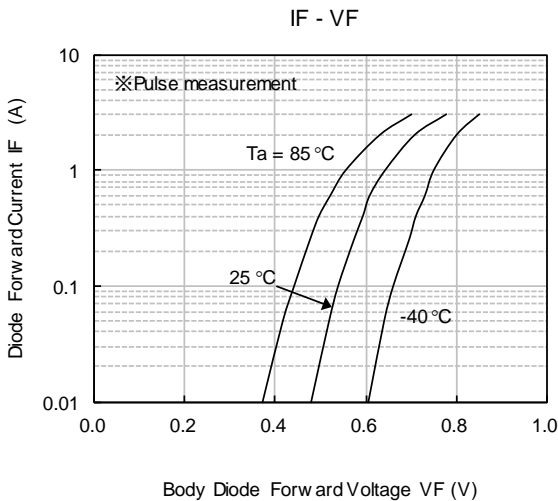
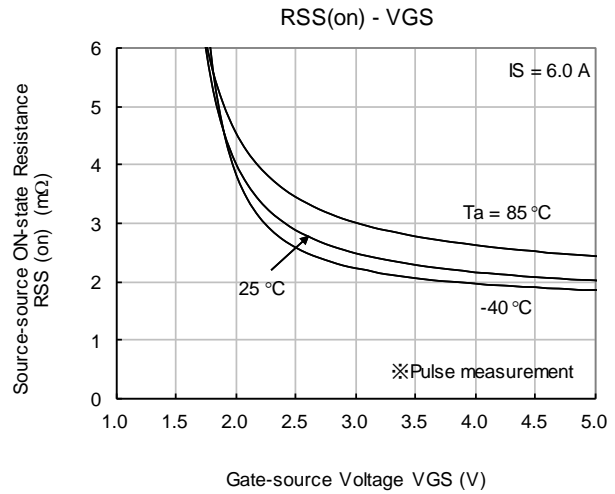
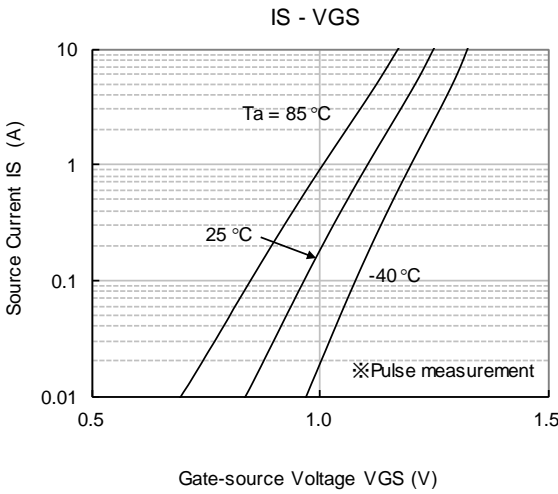
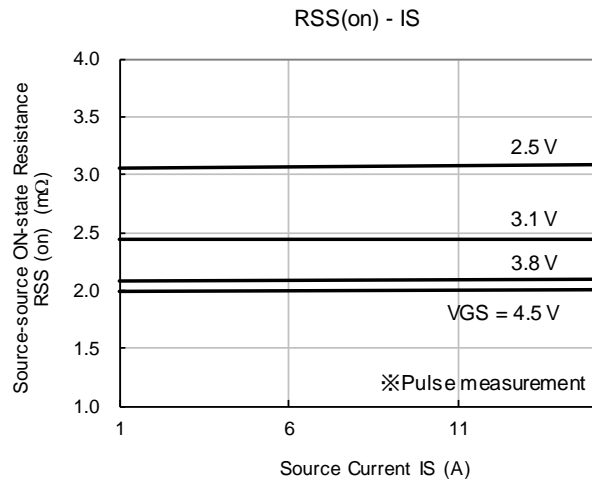
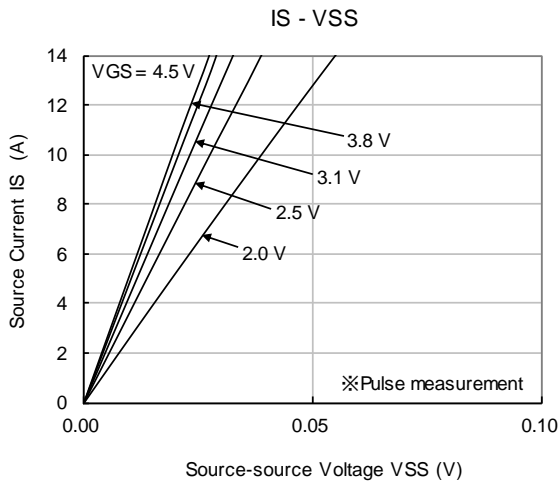
Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

*1 Guaranteed by design, not subject to production testing

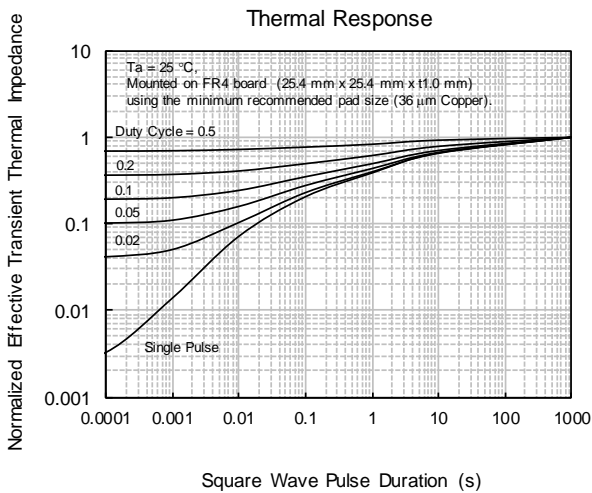
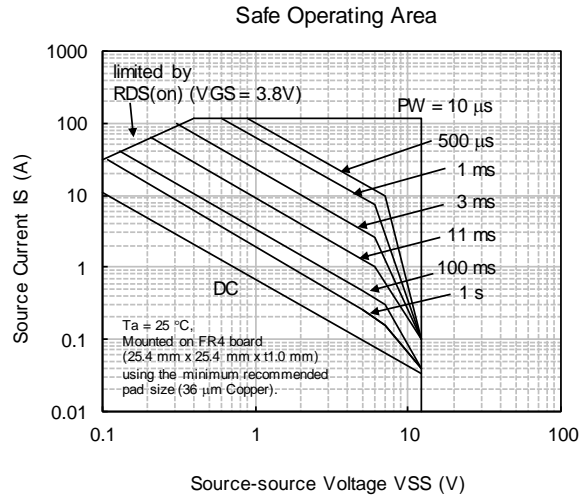
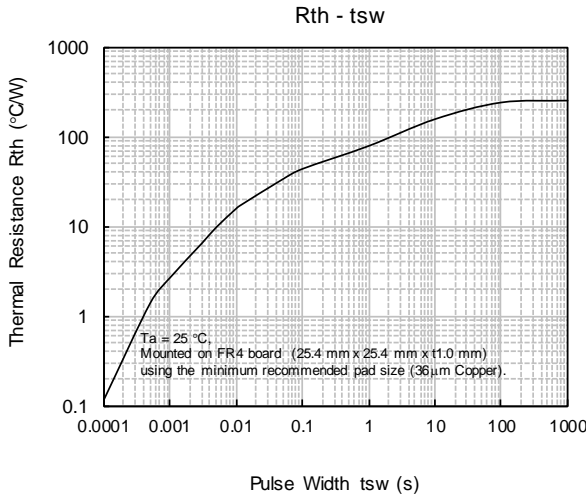
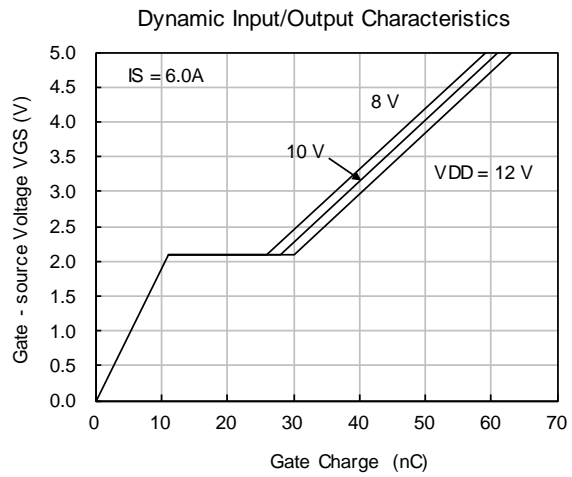
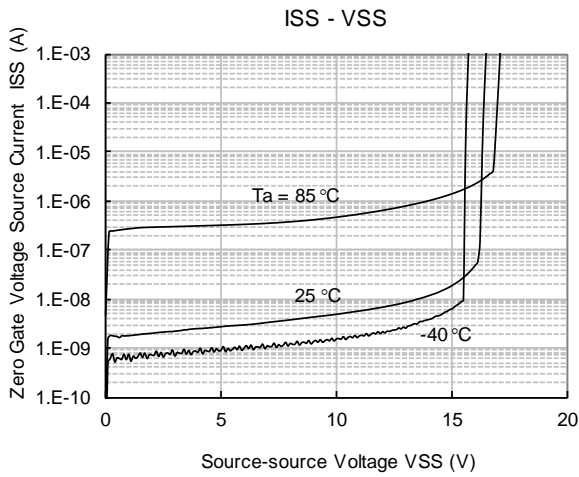
*2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time



8. TECHNICAL DATA (Reference)



TECHNICAL DATA (Reference)



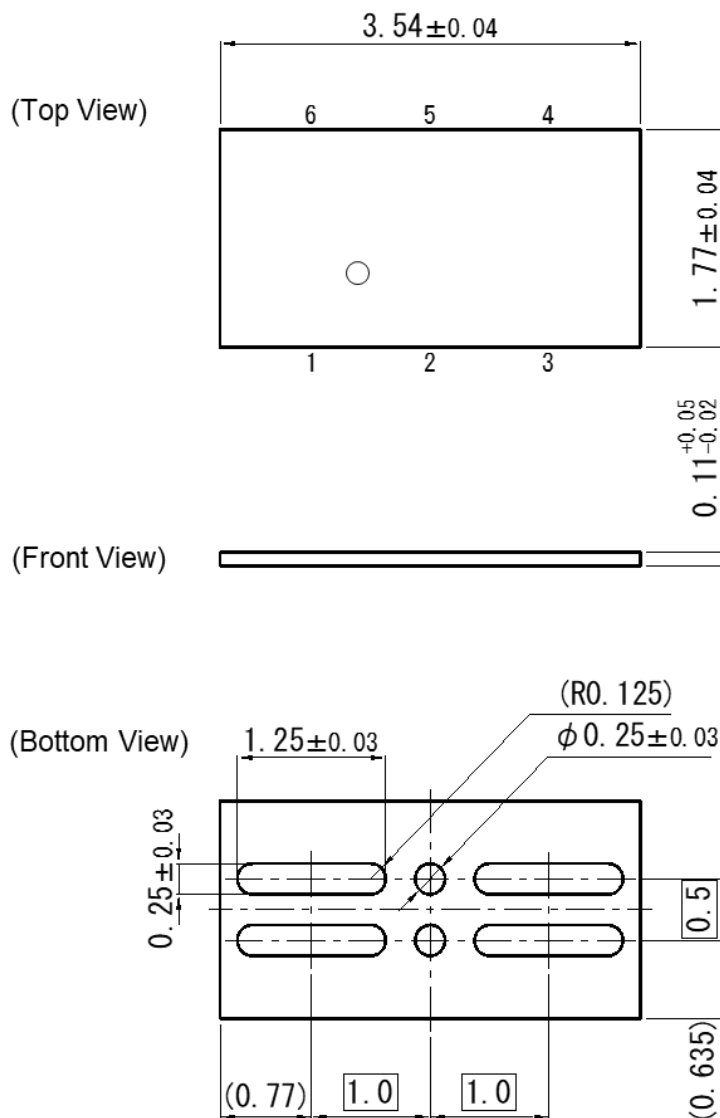
Destruction Current

	Condition	Result
Operation test	$V_{GS}=3.8\text{V}$ $t=3\text{ms}, I_S=40\text{A}$	PASS
	$V_{GS}=3.8\text{V}$ $t=11\text{ms}, I_S=15\text{A}$	PASS
Destruction current	$V_{GS}=3.8\text{V}$ $t=3\text{ms}$	110A
	$V_{GS}=3.8\text{V}$ $t=11\text{ms}$	78A

$T_a = 25^\circ\text{C}$,
Mounted on FR4 board (25.4 mm x 25.4 mm x 1.0 mm)
using the minimum recommended pad size (36 μm Copper).

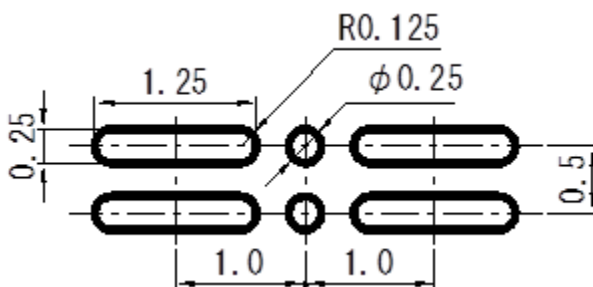
9. OUTLINE

Unit : mm



10. LAND PATTERN (Reference)

Unit : mm



11. REVISION HISTORY

Date	Revision	Description
2021.2.8	1.00	1. initially issued.

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